

30V P-Channel MOSFET



SOT-26

Pin Definition:

1. Drain

6. Drain

2. Drain

5. Drain

3. Gate

4. Source

Key Parameter Performance

Parameter		Value	Unit	
V_{DS}		-30	V	
R _{DS(on)} (max)	V _{GS} = -10V	60	mΩ	
	$V_{GS} = -4.5V$	100		
Q_g		9.52	nC	

Features

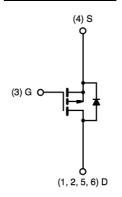
- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Ordering Information

Part No.	Package	Packing
TSM3457CX6 RFG	SOT-26	3kpcs / 7" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



P-Channel MOSFET

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current		I _D	-5	Α
Pulsed Drain Current		I _{DM}	-20	Α
Continuous Source Current (Diode Con	duction) (Note 1,2)	I _S	-1.7	А
Maximum Power Dissipation	T _A =25°C	P _D	2.0	W
	T _A =70°C		1.3	
Operating Junction Temperature		TJ	+150	°C
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R_{ ext{ iny GJC}}$	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	R _{eJA}	80	°C/W

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Electrical Specifications (T_A = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static (Note 3)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV _{DSS}	-30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1.0	-1.5	-3.0	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -24V, V_{GS} = 0V$	I _{DSS}			-1.0	μΑ
On-State Drain Current	$V_{DS} = -5V, V_{GS} = -10V$	I _{D(ON)}	-20			Α
Dunin Course On Otata Banistana	$V_{GS} = -4.5V$, $I_{D} = -3.7A$			82	100	mΩ
Drain-Source On-State Resistance	$V_{GS} = -10V, I_D = -5A$	$R_{DS(ON)}$		50	60	
Forward Transconductance	$V_{DS} = -15V, I_{D} = -5A$	g _{fs}		10		S
Diode Forward Voltage	$I_S = -1.7A, V_{GS} = 0V$	V _{SD}		-0.8	-1.2	V
Dynamic (Note 4,5)		•				
Total Gate Charge		Q_g		9.52		
Gate-Source Charge	$V_{DS} = -15V, I_D = -3.7A,$ $V_{GS} = -10V$	Q_gs		3.43		nC
Gate-Drain Charge		Q_{gd}		1.71]
Input Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}		551.57		
Output Capacitance		C _{oss}		90.96		рF
Reverse Transfer Capacitance		C _{rss}		60.79		
Switching (Note 4,5)						
Turn-On Delay Time	$V_{DD} = -15V, \ R_L = 15\Omega, \\ I_D = -1A, \ V_{GEN} = -10V, \\ R_G = 6\Omega$	t _{d(on)}		10.8		
Turn-On Rise Time		t _r		2.33		
Turn-Off Delay Time		t _{d(off)}		22.53		ns
Turn-Off Fall Time		t _f		3.87		

Notes:

- 1. Pulse width limited by the Maximum junction temperature
- 2. Surface Mounted on FR4 Board, t ≤ 5 sec.
- 3. pulse test: PW \leq 300 μ S, duty cycle \leq 2%
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.

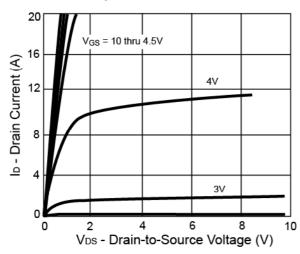


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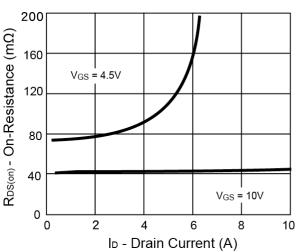


Electrical Characteristics Curves

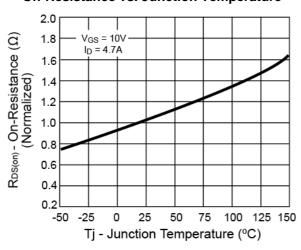
Output Characteristics



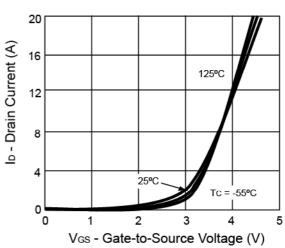
On-Resistance vs. Drain Current



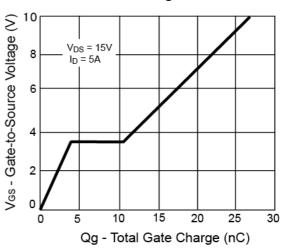
On-Resistance vs. Junction Temperature



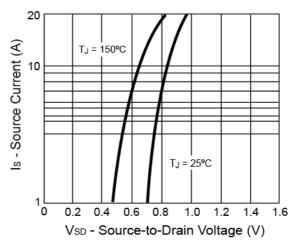
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



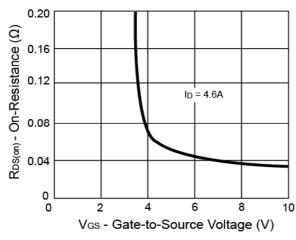


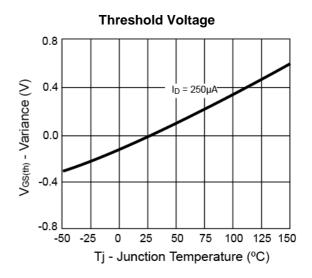
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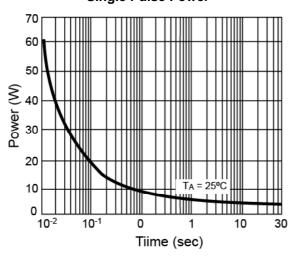
Electrical Characteristics Curves

On-Resistance vs. Gate-Source Voltage

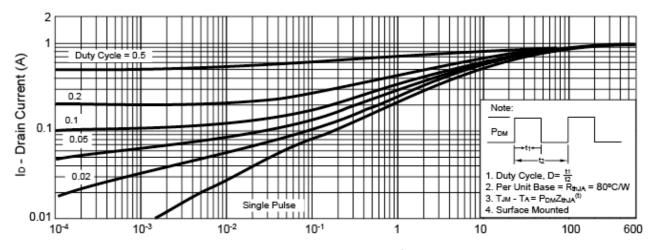




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

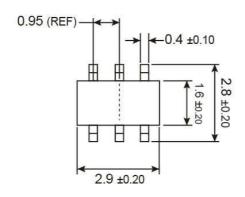


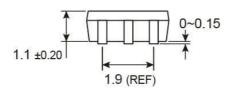
Square Wave Pulse Duration (sec)

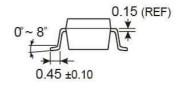




SOT-26 Mechanical Drawing







Unit: Millimeters

Marking Diagram



57 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr S =May T =Jun U =Jul V =Aug

W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code



TSM3457 30V P-Channel MOSFET

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